



**DIODES, MICROWAVE, SILICON,
TUNING VARACTOR,
BASED ON TYPES ML4336 THRU ML4343
ESCC Detail Specification No. 5512/005**

Issue 2	March 2013
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DCR No.	CHANGE DESCRIPTION
772	Specification upissued to incorporate editorial changes per DCR.

TABLE OF CONTENTS

1	GENERAL	6
1.1	SCOPE	6
1.2	TYPE VARIANTS	6
1.3	MAXIMUM RATINGS	6
1.4	PARAMETER DERATING INFORMATION	6
1.5	PHYSICAL DIMENSIONS	6
1.6	FUNCTIONAL DIAGRAM	6
1.7	HANDLING PRECAUTIONS	6
2	APPLICABLE DOCUMENTS	6
3	TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS	6
4	REQUIREMENTS	16
4.1	GENERAL	16
4.2	DEVIATIONS FROM GENERIC SPECIFICATION	16
4.2.1	Deviations from Special In-process Controls	16
4.2.2	Deviations from Final Production Tests (Chart II)	16
4.2.3	Deviations from Burn-in and Electrical Measurements (Chart III)	16
4.2.4	Deviations from Qualification Tests (Chart IV)	16
4.2.5	Deviations from Lot Acceptance Tests (Chart V)	16
4.3	MECHANICAL AND ENVIRONMENTAL REQUIREMENTS	17
4.3.1	Dimension Check	17
4.3.2	Weight	17
4.3.3	Terminal Strength	17
4.4	MATERIALS AND FINISHES	18
4.4.1	Case	18
4.4.2	Lead Materials and Finish	18
4.5	MARKING	18
4.5.1	General	18
4.5.2	Cathode Identification	18
4.5.3	The ESCC Component Number	18
4.5.4	Traceability Information	19
4.6	ELECTRICAL MEASUREMENTS	19
4.6.1	Electrical Measurements at Room Temperature	19
4.6.2	Electrical Measurements at High and Low Temperatures	19
4.6.3	Circuits for Electrical Measurements	19
4.7	BURN-IN TESTS	19

4.7.1	Parameter Drift Values	19
4.7.2	Conditions for High Temperature Reverse Bias Burn-in	19
4.7.3	Conditions for Power Burn-in	19
4.7.4	Electrical Circuits for High Temperature Reverse Bias and Power Burn-in	19
4.8	ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESCC GENERIC SPECIFICATION NO. 5010)	23
4.8.1	Electrical Measurements on Completion of Environmental Tests	23
4.8.2	Electrical Measurements at Intermediate Points and on Completion of Endurance Tests	23
4.8.3	Conditions for Operating Life Tests (Part of Endurance Testing)	23
4.8.4	Electrical Circuits for Operating Life Tests	23
4.9	TOTAL DOSE IRRADIATION TESTING	23
4.9.1	Application	23
4.9.2	Bias Conditions	23
4.9.3	Electrical Measurements	23
4.10	SPECIAL TESTING	23
APPENDIX A		26

1 **GENERAL**

1.1 **SCOPE**

This specification details the ratings, physical and electrical characteristics, test and inspection data for a Diode, Microwave, Silicon, Tuning Varactor, based on Types ML4336 thru ML4343. It shall be read in conjunction with ESCC Generic Specification No. 5010, the requirements of which are supplemented herein.

1.2 **TYPE VARIANTS**

Variants of the basic diodes specified herein, which are also covered by this specification are given in Table 1(a).

1.3 **MAXIMUM RATINGS**

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the diodes specified herein, are as scheduled in Table 1(b).

1.4 **PARAMETER DERATING INFORMATION**

The derating information applicable to the diodes specified herein is shown in Figure 1.

1.5 **PHYSICAL DIMENSIONS**

The physical dimensions of the diodes specified herein are shown in Figure 2.

1.6 **FUNCTIONAL DIAGRAM**

The functional diagram, showing lead identification, of the diodes specified herein, is shown in Figure 3.

1.7 **HANDLING PRECAUTIONS**

These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are Categorised as Class 2 with a Minimum Critical Path Failure Voltage of 3400V.

2 **APPLICABLE DOCUMENTS**

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5010 for Discrete Microwave Semiconductor Components.
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices.

3 **TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS**

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

TABLE 1(a) – TYPE VARIANTS

(1) Variant	(2) Based On Type	(3) Figure	(4) Total Capacitance C_T (pF)		(5) Quality Factor (Q) (Minimum)	(6) Body-Lid And Lead Material And Finish
			Min	Max		
1	ML4336 - 30	2(a)	2.3	3.1	1350	A7-D2
2	ML4336 - 31	2(b)	2.3	3.1	1350	A7-D2
3	ML4336 - 36	2(c)	2.3	3.1	1350	A7-D2
4	ML4336 - 103	2(d)	2.4	3.2	1350	A7-D2
5	ML4336 - 118	2(e)	2.34	3.14	1350	A7
6	ML4336 - 186	2(f)	2.25	3.05	1350	D2
7	ML4337 - 30	2(a)	2.85	3.75	1200	A7-D2
8	ML4337 - 31	2(b)	2.85	3.75	1200	A7-D2
9	ML4337 - 36	2(c)	2.85	3.75	1200	A7-D2
10	ML4337 - 103	2(d)	2.95	3.85	1200	A7-D2
11	ML4337 - 118	2(e)	2.89	3.79	1200	A7
12	ML4337 - 186	2(f)	2.8	3.7	1200	D2
13	ML4338 - 30	2(a)	3.4	4.4	1100	A7-D2
14	ML4338 - 31	2(b)	3.4	4.4	1100	A7-D2
15	ML4338 - 36	2(c)	3.4	4.4	1100	A7-D2
16	ML4338 - 103	2(d)	3.5	4.5	1100	A7-D2
17	ML4338 - 118	2(e)	3.44	4.44	1100	A7
18	ML4338 - 186	2(f)	3.35	4.35	1100	D2
19	ML4339 - 30	2(a)	4.1	5.3	1000	A7-D2
20	ML4339 - 31	2(b)	4.1	5.3	1000	A7-D2
21	ML4339 - 36	2(c)	4.1	5.3	1000	A7-D2
22	ML4339 - 103	2(d)	4.2	5.4	1000	A7-D2
23	ML4339 - 118	2(e)	4.14	5.34	1000	A7
24	ML4339 - 186	2(f)	4.05	5.25	1000	D2
25	ML4340 - 30	2(a)	4.9	6.3	1000	A7-D2
26	ML4340 - 31	2(b)	4.9	6.3	1000	A7-D2
27	ML4340 - 36	2(c)	4.9	6.3	1000	A7-D2
28	ML4340 - 103	2(d)	5	6.4	1000	A7-D2
29	ML4340 - 118	2(e)	4.94	6.34	1000	A7
30	ML4340 - 186	2(f)	4.85	6.25	1000	D2
31	ML4341 - 30	2(a)	5.9	7.7	900	A7-D2
32	ML4341 - 31	2(b)	5.9	7.7	900	A7-D2
33	ML4341 - 36	2(c)	5.9	7.7	900	A7-D2
34	ML4341 - 103	2(d)	6	7.8	900	A7-D2
35	ML4341 - 118	2(e)	5.94	7.74	900	A7
36	ML4341 - 186	2(f)	5.85	7.65	900	D2
37	ML4342 - 30	2(a)	7.2	9.2	850	A7-D2

(1) Variant	(2) Based On Type	(3) Figure	(4) Total Capacitance C_T (pF)		(5) Quality Factor (Q) (Minimum)	(6) Body-Lid And Lead Material And Finish
			Min	Max		
38	ML4342 - 31	2(b)	7.2	9.2	850	A7-D2
39	ML4342 - 36	2(c)	7.2	9.2	850	A7-D2
40	ML4342 - 103	2(d)	7.3	9.3	850	A7-D2
41	ML4342 - 118	2(e)	7.24	9.24	850	A7
42	ML4342 - 186	2(f)	7.15	9.15	850	D2
43	ML4343 - 30	2(a)	8.7	11.3	800	A7-D2
44	ML4343 - 31	2(b)	8.7	11.3	800	A7-D2
45	ML4343 - 36	2(c)	8.7	11.3	800	A7-D2
46	ML4343 - 103	2(d)	8.8	11.4	800	A7-D2
47	ML4343 - 118	2(e)	8.74	11.34	800	A7
48	ML4343 - 186	2(f)	8.65	11.25	800	D2

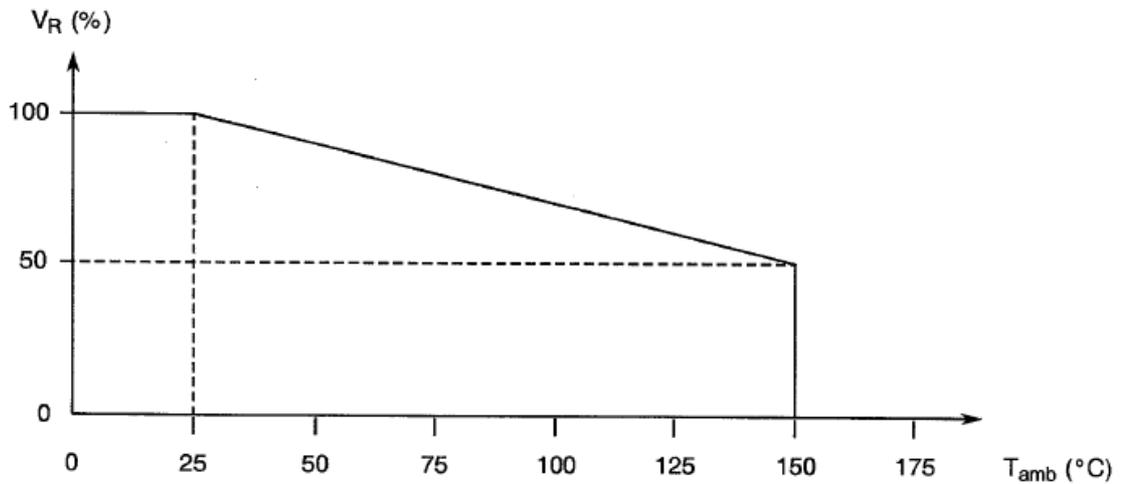
TABLE 1(b) - MAXIMUM RATINGS

No.	Characteristics	Symbol	Maximum Ratings	Unit	Remarks
1	DC Reverse Voltage	V_R	-40	V	Note 1
2	Operating Temperature Range	T_{op}	-65 to +150	°C	T_{amb}
3	Storage Temperature Range	T_{stg}	-65 to +150	°C	
4	Soldering Temperature	T_{sol}	+230	°C	Note 2

NOTES

1. Measured at $I_R = 10\mu A$ and $T_{amb} = +25^\circ C$. For derating at $T_{amb} > +25^\circ C$, see Figure 1.
2. Duration 5 seconds maximum (at a distance of not less than 1.5mm from the body for Variants 06, 12, 18, 24, 30, 36, 42 and 48) and the same termination shall not be resoldered until 3 minutes have elapsed.

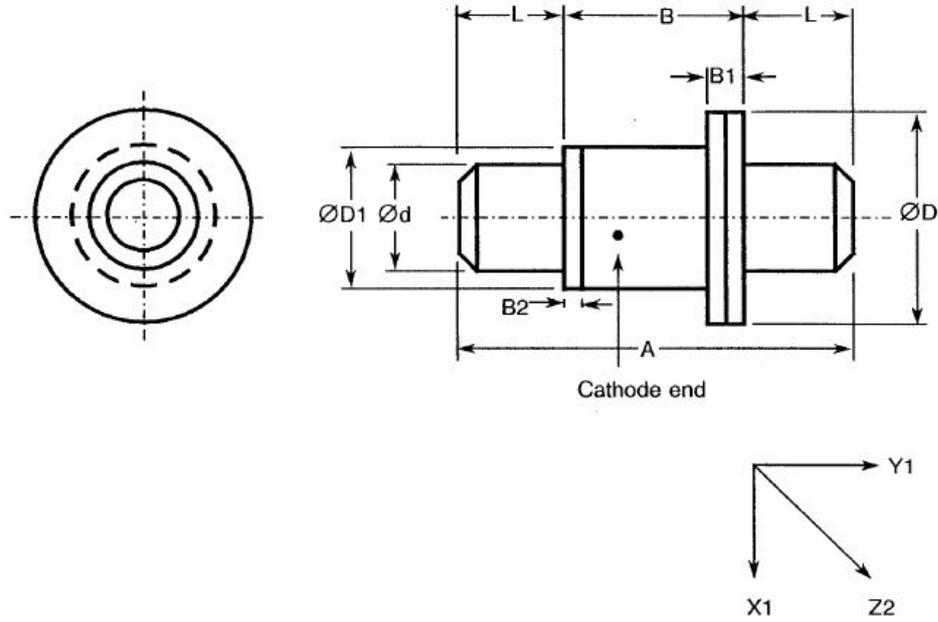
FIGURE 1 - PARAMETER DERATING INFORMATION



V_R versus Temperature

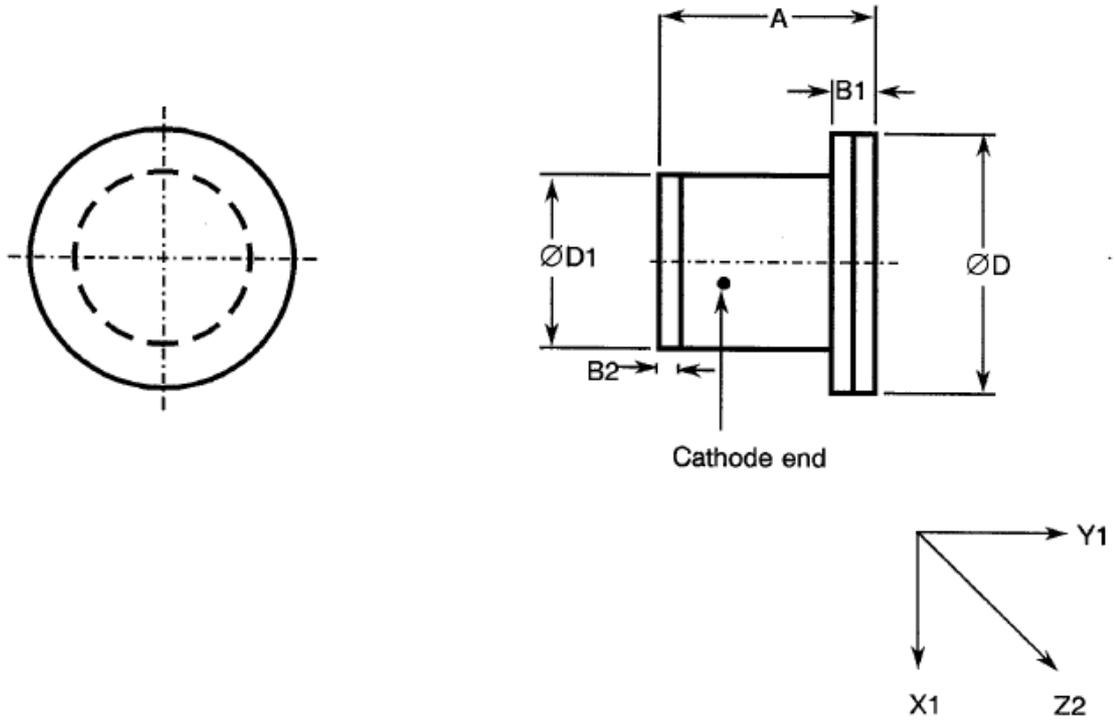
FIGURE 2 – PHYSICAL DIMENSIONS

FIGURE 2(a) - VARIANTS 01, 07, 13, 19, 25, 31, 37, 43



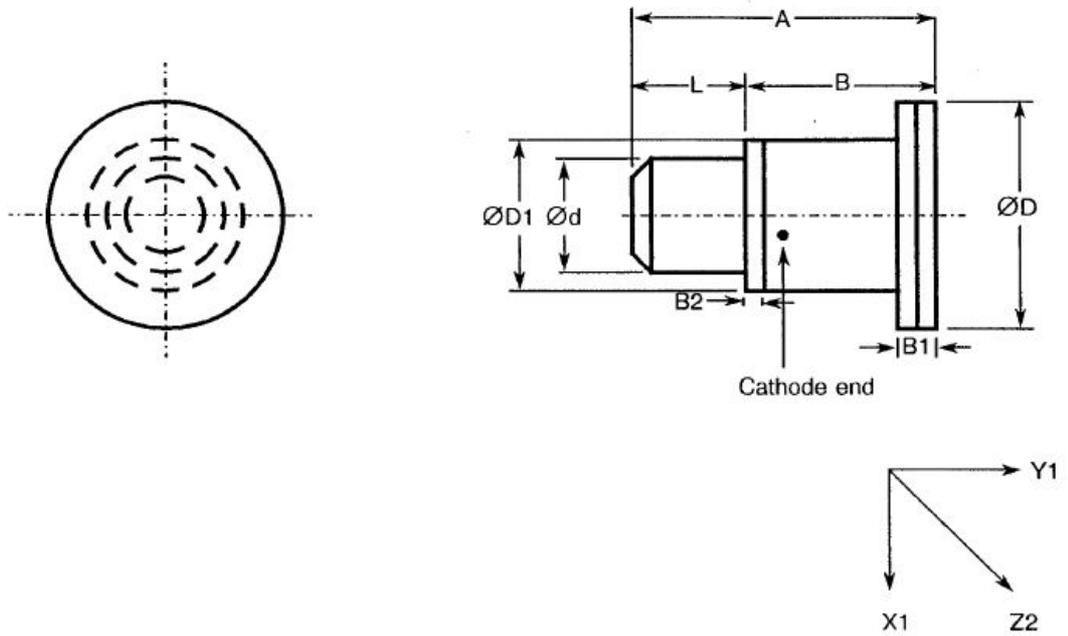
Symbol	Millimetres	
	Min	Max
A	5.2	5.72
B	2.16	2.46
B1	0.41	0.61
B2	0.15	0.25
$\varnothing d$	1.52	1.63
$\varnothing D$	3	3.23
$\varnothing D1$	1.95	2.11
L	1.52	1.63

FIGURE 2(b) - VARIANTS 02, 08, 14, 20, 26, 32, 38, 44



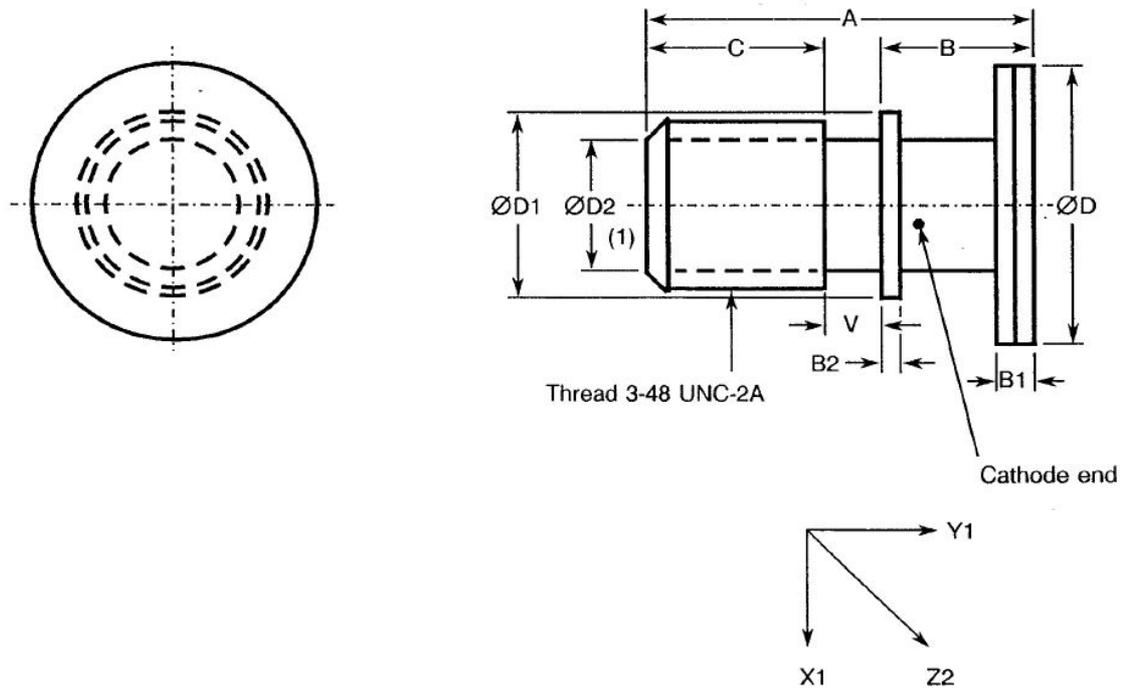
Symbol	Millimetres	
	Min	Max
A	2.16	2.46
B1	0.41	0.61
B2	0.15	0.25
$\varnothing D$	3	3.23
$\varnothing D1$	1.95	2.11

FIGURE 2(c) – VARIANTS 03, 09, 15, 21, 27, 33, 39, 45



Symbol	Millimetres	
	Min	Max
A	3.6	4.18
B	2.16	2.46
B1	0.41	0.61
B2	0.15	0.25
$\varnothing d$	1.52	1.63
$\varnothing D$	3	3.23
$\varnothing D1$	1.95	2.11
L	1.52	1.63

FIGURE 2(d) – VARIANTS 04, 10, 16, 22, 28, 34, 40, 46

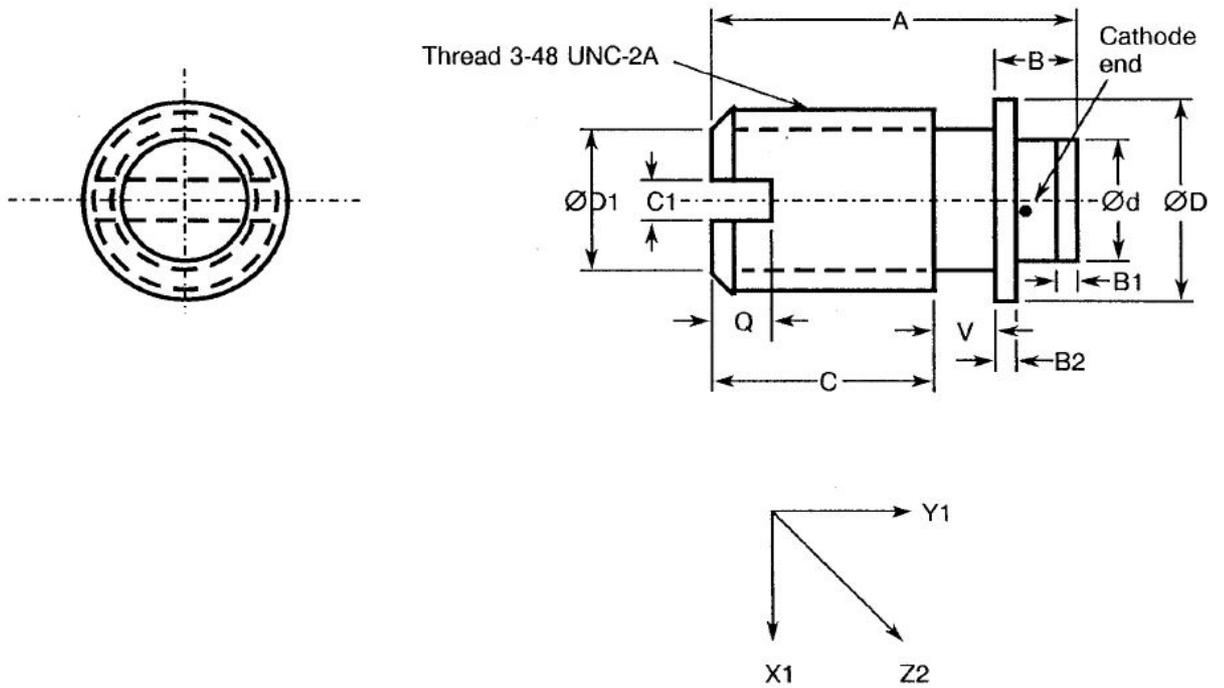


Symbol	Millimetres	
	Min	Max
A	4.71	5.3
B	1.47	1.8
B1	0.41	0.61
B2	0.2	0.3
C	1.97	3.19
ØD	3	3.23
ØD1	2.49	2.59
ØD2	1.6	2
V	0.64	0.94

NOTES

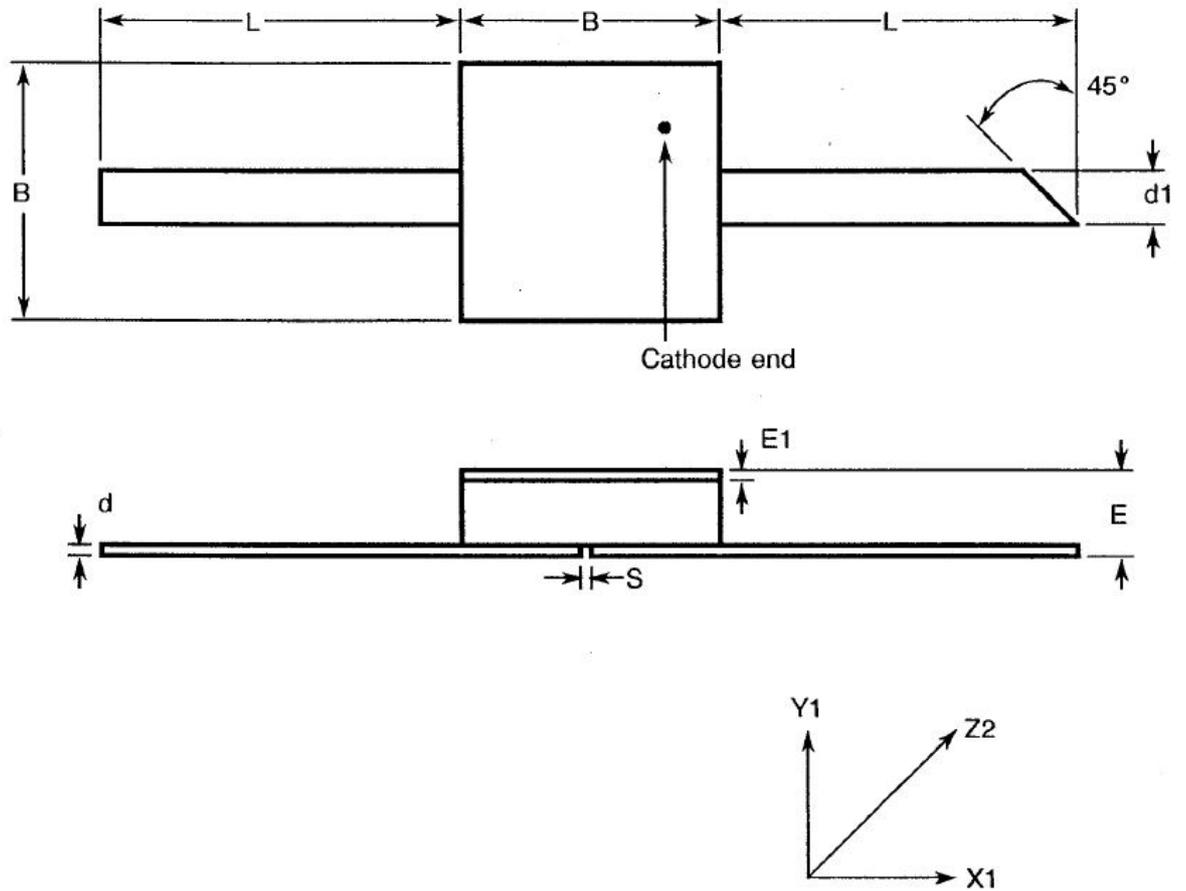
1. 6 spline socket, 1.39mm deep.

FIGURE 2(e) – VARIANTS 05, 11, 17, 23, 29, 35, 41, 47

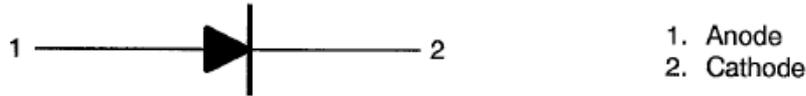


Symbol	Millimetres	
	Min	Max
A	4.19	4.7
B	0.77	1.04
B1	0.2	0.3
B2	0.22	0.28
C	2.21	3.29
C1	0.38	0.64
Ød	1.22	1.32
ØD	2.49	2.59
ØD1	1.6	2
Q	0.64	1.14
V	0.64	0.94

FIGURE 2(f) – VARIANTS 06, 12, 18, 24, 30, 36, 42, 48



Symbol	Millimetres	
	Min	Max
B	2.39	2.62
d	0.07	0.15
d1	0.48	0.56
E	0.79	1.12
E1	0.1	0.18
L	3.3	5.84
S	0.1	-

FIGURE 3 – FUNCTIONAL DIAGRAM**NOTES**

1. The cathode end shall be marked with a black dot or band. The marking will not be on the cathode connection but adjacent to it.

4 REQUIREMENTS**4.1 GENERAL**

The complete requirements for procurement of the diodes specified herein are stated in this specification and ESCC Generic Specification No. 5010 for Discrete Microwave Semiconductor Components. Deviations from the Generic Specification, applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION**4.2.1 Deviations from Special In-process Controls**

- (a) Para. 5.2.3, Total Dose Irradiation Testing: Shall be performed during qualification and extension of qualification.
- (b) Para. 5.2.3, Total Dose Irradiation Testing: Shall be performed during procurement on a lot acceptance basis at the total dose irradiation level specified in the purchase order.
- (c) Quality Factor Measurement (Q): 3 randomly chosen samples shall be encapsulated in the type of package shown in Figure 2(a) of this specification. After encapsulation, Quality Factor measurements shall be performed using the method shown in Figure 4 of this specification with $V_R = -4V$. The limits specified in Table 1(a) of this specification shall be met.

4.2.2 Deviations from Final Production Tests (Chart II)

None.

4.2.3 Deviations from Burn-in and Electrical Measurements (Chart III)

- (a) Para. 9.21, High Temperature Reverse Bias Burn-in: Shall be performed at 50% of rated V_R .

4.2.4 Deviations from Qualification Tests (Chart IV)

- (a) Para. 9.23, Special Testing: Shall not be performed.

4.2.5 Deviations from Lot Acceptance Tests (Chart V)

- (a) Para. 9.23, Special Testing: Shall not be performed.

4.3 MECHANICAL AND ENVIRONMENTAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the diodes specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the diodes specified herein shall be:

Variant No.	Weight (g)
01, 07, 13, 19, 25, 31, 37, 43	0.12
02, 08, 14, 20, 26, 32, 38, 44	0.06
03, 09, 15, 21, 27, 33, 39, 45	0.1
04, 05, 10, 11, 16, 17, 22, 23, 28, 29, 34, 35, 40, 41, 46, 47	0.14
06, 12, 18, 24, 30, 36, 42, 48	0.06

4.3.3 Terminal Strength

The requirements for terminal strength testing are specified in Section 9 of ESCC Generic Specification No. 5010. The test conditions shall be as follows:

- (a) Condition: 'A' (Tension)
 - Variants 06, 12, 18, 24, 30, 36, 42 and 48:
 - Force: 5.1N.
 - Duration: 5 seconds.
- (b) Condition: 'D2' (Stud Torque)
 - Variants 04, 10, 16, 22, 28, 34, 40 and 46:
 - Torque: 56mNm.
 - Duration: 5 seconds.
 - Variants 05, 11, 17, 23, 29, 35, 41 and 47:
 - Torque: 42mNm.
 - Duration: 5 seconds.
- (c) Condition: Compression
 - Variants 01, 02, 03, 04, 07, 08, 09, 10, 13, 14, 15, 16, 19, 20, 21, 22, 25, 26, 27, 28, 31, 32, 33, 34, 37, 38, 39, 40, 43, 44, 45 and 46:
 - Force: 50N.
 - Duration: 5 seconds.
 - Variants 05, 11, 17, 23, 29, 35, 41 and 47:
 - Force: 10N.
 - Duration: 5 seconds.

The compression test shall be performed by applying the specified force to the end-cap by means of a suitable weight applied for the specified time. On completion of the test, a visual examination shall be performed to check for damage to the end-cap or the ceramic body.

4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the diodes specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material shall not guarantee acceptance of the finished product.

4.4.1 Case

The case shall be hermetically sealed and have a ceramic body. The lid shall be brazed, welded or preform soldered.

4.4.2 Lead Materials and Finish

- (a) For Variants 01, 02, 03, 04, 07, 08, 09, 10, 13, 14, 15, 16, 19, 20, 21, 22, 25, 26, 27, 28, 31, 32, 33, 34, 37, 38, 39, 40, 43, 44, 45 and 46, the body material shall be Type 'A' with Type '7' finish and the lid material shall be Type 'D' with Type '2' finish, in accordance with the requirements of ESCC Basic Specification No. 23500.
- (b) For Variants 05, 11, 17, 23, 29, 35, 41 and 47, the lead material shall be Type 'A' with Type '7' finish in accordance with the requirements of ESCC Basic Specification No. 23500.
- (c) For Variants 06, 12, 18, 24, 30, 36, 42 and 48, the lead material shall be Type 'D' with Type '2' finish in accordance with the requirements of ESCC Basic Specification No. 23500.

4.5 MARKING

4.5.1 General

The marking of components delivered to this specification shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and the following paragraphs. When the component is too small to accommodate all of the marking specified, as much as space permits shall be marked and the marking information, in full, shall accompany the component in its primary package.

The information to be marked and the order of precedence, shall be as follows:

- (a) Cathode Identification.
- (b) The ESCC Component Number.
- (c) Traceability Information.

4.5.2 Cathode Identification

Cathode identification shall be as shown in Figures 2 and 3 of this specification.

4.5.3 The ESCC Component Number

Each component shall bear the ESCC Component Number which shall be constituted and marked as follows:

Example: 551200501BF

- Detail Specification Number: 5512005
- Type Variant (see Table 1(a)): 01
- Testing Level (B or C, as applicable): B
- Total Dose Irradiation Level (if applicable): F

The Total Dose Irradiation Level designation shall be added for those devices for which a sample has been successfully tested to the level in question. For these devices, a code letter shall be added in accordance with the requirements of ESCC Basic Specification No. 22900.

4.5.4 Traceability Information

Each component shall be marked in respect of traceability information as defined in ESCC Basic Specification No. 21700.

4.6 ELECTRICAL MEASUREMENTS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured at room temperature are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}\text{C}$.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. Unless otherwise specified, the measurements shall be performed at $T_{amb} = +150 (+0 -3)^{\circ}\text{C}$.

4.6.3 Circuits for Electrical Measurements

A circuit for use in performing the Quality Factor measurement is shown in Figure 4.

4.7 BURN-IN TESTS

Burn-in shall be Category 1 of Chart III(a).

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}\text{C}$. The parameter drift values (Δ) applicable to the scheduled parameters shall not be exceeded. In addition to these drift value requirements for a given parameter, the appropriate limit value specified in Table 2 shall not be exceeded.

4.7.2 Conditions for High Temperature Reverse Bias Burn-in

The requirements for the high temperature reverse bias burn-in are specified in Section 7 of ESCC Generic Specification No. 5010. The conditions for high temperature reverse bias burn-in shall be as specified in Table 5(a) of this specification.

4.7.3 Conditions for Power Burn-in

The requirements for power burn-in are specified in Section 7 of ESCC Generic Specification No. 5010. The conditions for power burn-in shall be as specified in Table 5(b) of this specification.

4.7.4 Electrical Circuits for High Temperature Reverse Bias and Power Burn-in

Circuits for use in performing the H.T.R.B and power burn-in tests are shown in Figures 5(a) and 5(b) of this specification.

TABLE 2 – ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE – DC PARAMETERS

No.	Characteristics	Symbol	MIL-STD-750 Test Method	Test Conditions	Limits		Unit
					Min.	Max.	
1	Reverse Current 1	I _{R1}	4016	V _R = -40V	-	10	μA
2	Reverse Current 2	I _{R2}	4016	V _R = -20V	-	50	nA
3	Forward Voltage	V _F	4011	I _F = 100mA	-	1	V

TABLE 2 – ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE – AC PARAMETERS

No.	Characteristics	Symbol	MIL-STD-750 Test Method	Test Conditions	Limits		Unit
					Min.	Max.	
4	Total Capacitance	C _T	4001	V _R = -4V f = 1MHz	Note 1		pF
5	Total Capacitance Ratio	-	4001	V _R = 0V V _R = -40V f = 1MHz Note 2 Variants 01 to 06 Variants 07 to 12 Variants 13 to 18 Variants 19 to 30 Variants 31 to 36 Variants 37 to 48	5.5 5.7 5.8 6 6.2 6.3	- - - - - -	

NOTES

1. See Column 4 of Table 1(a).

$$2. \text{Ratio} = \frac{C_T \text{ at } V_R = 0V}{C_T \text{ at } V_R = -40V}$$

TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES

No.	Characteristics	Symbol	Spec. And/Or Test Method	Test Condition	Limits		Unit
					Min.	Max.	
2	Reverse Current 2	I _{R2}	As per Table 2	As per Table 2	-	10	μA

TABLE 4- PARAMETER DRIFT VALUES

No.	Characteristics	Symbol	Spec. And/Or Test Method	Test Condition	Change Limits (Δ)	Unit
2	Reverse Current 2	I_{R2}	As per Table 2	As per Table 2	± 10 (1) or (2) ± 100 (1)	nA %
3	Forward Voltage	V_F	As per Table 2	As per Table 2	± 100 (1)	mV

NOTES

- $\Delta 1 = \Delta 2$.
- Whichever is the greater, referred to the initial measurement.

FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

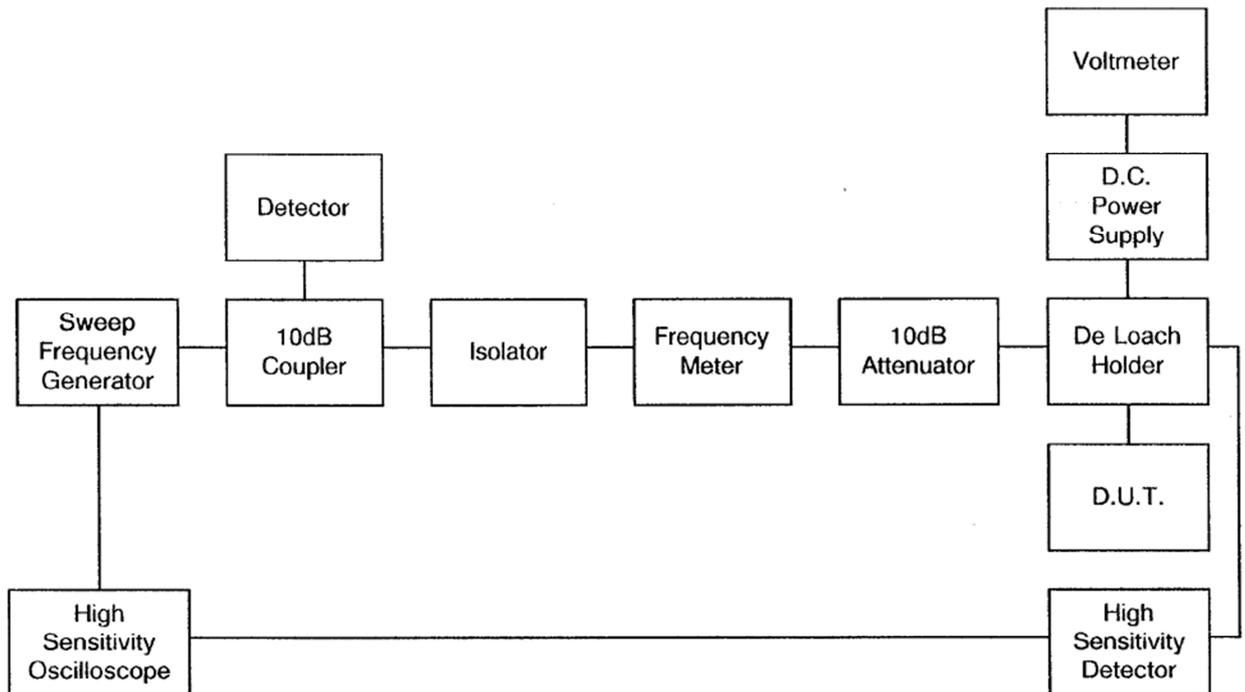


TABLE 5(a) - CONDITIONS FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN AND OPERATING LIFE TESTS

No.	Characteristics	Symbol	Conditions	Unit
1	Ambient Temperature	T_{amb}	+ 150 (+0 -3)	°C
2	Reverse Voltage	V_R	-20	V

TABLE 5(b) - CONDITIONS FOR POWER BURN-IN

No.	Characteristics	Symbol	Conditions	Unit
1	Ambient Temperature	T_{amb}	+ 125 (+0 -3)	°C
2	Forward Current	I_F	25	mA

FIGURE 5(a) - ELECTRICAL CIRCUIT FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN AND OPERATING LIFE TESTS

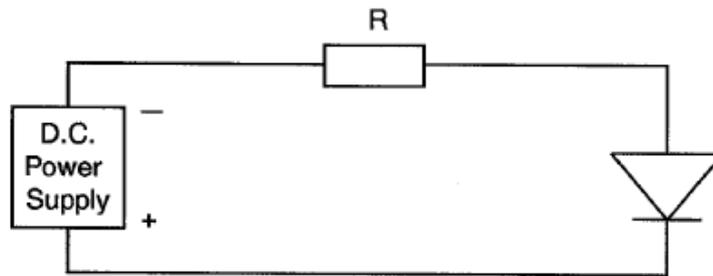
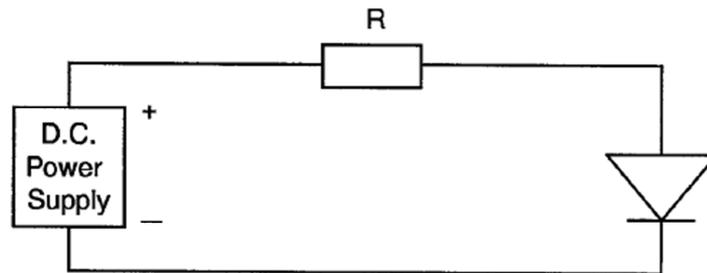


FIGURE 5(b) - ELECTRICAL CIRCUIT FOR POWER BURN-IN



4.8 ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESCC GENERIC SPECIFICATION No. 5010)

4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 2. Unless otherwise stated, the measurements shall be performed at $T_{amb} = + 22 \pm 3^{\circ}\text{C}$.

4.8.2 Electrical Measurements at Intermediate Points and on Completion of Endurance Tests

The parameters to be measured at intermediate points and on completion of endurance tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}\text{C}$.

4.8.3 Conditions for Operating Life Tests (Part of Endurance Testing)

The requirements for operating life testing are specified in Section 9 of ESCC Generic Specification No. 5010. The conditions for operating life testing are specified in Table 5(a) of this specification.

4.8.4 Electrical Circuits for Operating Life Tests

The circuit to be used for performance of the operating life test shall be the same as shown in Figure 5(a) for High Temperature Reverse Bias Burn-in.

4.9 TOTAL DOSE IRRADIATION TESTING

4.9.1 Application

If specified in Para. 4.2.1 of this specification, total dose irradiation testing shall be performed in accordance with the requirements of ESCC Basic Specification No. 22900.

4.9.2 Bias Conditions

Continuous bias shall be applied during irradiation testing as shown in Figure 6 of this specification.

4.9.3 Electrical Measurements

The parameters to be measured prior to irradiation exposure are scheduled in Table 2 of this specification. Only devices which meet the requirements of Table 2 shall be included in the test sample.

The parameters to be measured during and on completion of irradiation testing are scheduled in Table 7 of this specification.

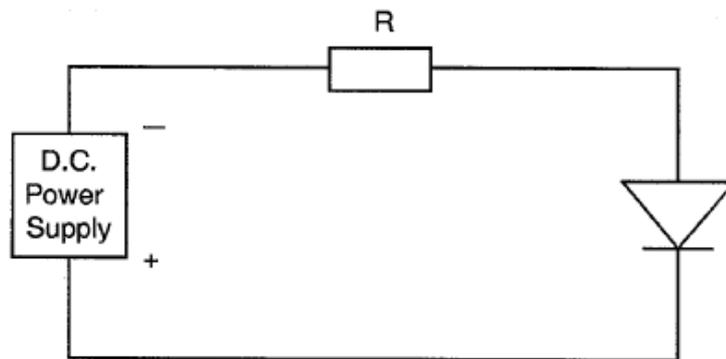
4.10 SPECIAL TESTING

Not applicable.

TABLE 6 – MEASUREMENTS AND INSPECTIONS ON COMPLETION OF ENVIRONMENTAL AND ENDURANCE TESTING

No.	Characteristics	Symbol	Spec. And/Or Test Method	Test Conditions	Limits		Unit
					Min.	Max.	
1	Reverse Current 1	I_{R1}	As per Table 2	As per Table 2	As per Table 2		μA
2	Reverse Current 2	I_{R2}	As per Table 2	As per Table 2	As per Table 2		nA
3	Forward Voltage	V_F	As per Table 2	As per Table 2	As per Table 2		V
4	Total Capacitance	C_T	As per Table 2	As per Table 2	As per Table 2		pF

FIGURE 6 - BIAS CONDITIONS FOR IRRADIATION TESTING



NOTES

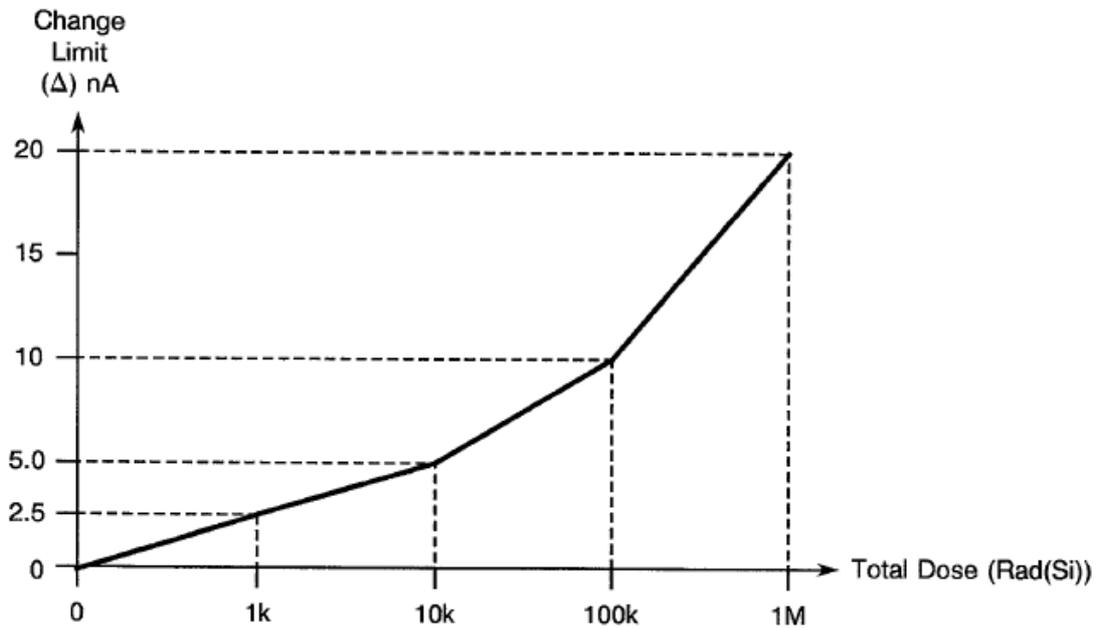
1. A reverse bias of $V_R = -20V$, shall be applied.

TABLE 7 - ELECTRICAL MEASUREMENTS DURING AND ON COMPLETION OF IRRADIATION TESTING

No.	Characteristics	Symbol	Spec. And/Or Test Method	Test Conditions	Change Limits (Δ)	Unit
2	Reverse Current 2	I_{R2}	As per Table 2	As per Table 2	Note 1	nA

NOTES

1. The graph given below shall be used to determine the maximum permitted change.



APPENDIX A**AGREED DEVIATIONS FOR M/A-COM LTD. (G.B.)**

Items Affected	Description of Deviations
Para. 4.2.2	Para. 9.4, "High Temperature Stabilisation Bake": May be performed at +150 (+0 -3)°C.